IN THE CLAIMS

Please cancel claims 1-16.

Please add the following claims.

--24. A film acoustic wave device manufactured according to a method comprising:

(a) forming a ground electrode intended to be placed on top of a semiconductor substrate which is made up of one of a plurality of pieces into which a wafer is divided;

(b) forming a piezoelectric thin film on top of the ground electrode; and

(c) forming at least one upper electrode on top of the piezoelectric thin film,

wherein a pattern of the film acoustic wave device is formed as a result of steps (a)-(c), and

wherein a shape of the pattern of the film acoustic wave device is dependent upon an intended position of the semiconductor substrate on the wafer.

25. The film acoustic wave device according to claim 24, wherein a length of the at least one upper electrode is dependent upon the intended position of the semiconductor substrate on the wafer.

C1 Cont
a3 Cont

26. The film acoustic wave device according to claim 24, wherein a width of the at least one upper electrode is dependent upon the intended position of the semiconductor substrate on the wafer.

27. The film acoustic wave device according to claim 24, wherein the step of forming at least one upper electrode comprises forms a plurality of upper electrodes, and

wherein distances between each of the plurality of upper electrodes is dependent upon the intended position of the semiconductor substrate on the wafer.

28. The film acoustic wave device according to claim 24, wherein said step (c) further includes a step,

(c1) connecting the at least one upper electrode to a bonding pad, and

wherein a shape of the bonding pad is dependent upon the intended position of the semiconductor substrate on the wafer.

29. The film acoustic wave device according to claim 28, wherein an area covered by the bonding pad is dependent upon the intended position of the semiconductor substrate on the wafer.

30. The film acoustic wave device according to claim 24, wherein said step (c) further includes steps,

(c1) connecting the at least one upper electrode to a bonding pad; and

(c2) connecting the at least one upper electrode and the bonding pad to a connecting pattern,

wherein a shape of the connecting pattern is dependent upon the intended position of the semiconductor substrate on the wafer.

31. The film acoustic wave device according to claim 30, wherein a length of the connecting pattern is dependent upon the intended position of the semiconductor substrate on the wafer.

32. The film acoustic wave device according to claim 30, wherein a width of the connecting pattern is dependent upon the intended position of the semiconductor substrate on the wafer.

33. The film acoustic wave device according to claim 24, wherein said step (c) further includes steps,

(c1) connecting the at least one upper electrode to a bonding pad; and

(c2) connecting the at least one upper electrode and the bonding pad to a connecting pattern,

wherein the connecting pattern is formed with an air bridge.

34. The film acoustic wave device according to claim 24, wherein the method according to which the device is manufactured includes a step,

(d) forming a capacitor on the same semiconductor substrate as the film acoustic wave device,

wherein a capacitance of the capacitor is dependent upon the intended position of the semiconductor substrate on the wafer.

35. The film acoustic wave device according to claim 24, wherein the semiconductor substrate is made of gallium arsenide (GaAs); the piezoelectric thin film is made of lead titanate ($PbTiO_3$); and the at least one upper electrode is a conductor substantially made of platinum (Pt).

36. The film acoustic wave device according to claim 24, wherein the semiconductor substrate is made of silicon (Si); the piezoelectric thin film is made of lead titanate ($PbTiO_3$); and the at least one upper electrode is a conductor substantially made of Platinum (Pt).

37. The film acoustic wave device according to claim 24, wherein the piezoelectric thin film is made of PZT ($PbTiO_3$-$PbZrO_3$); and the at least one upper electrode and the ground electrode is a conductor substantially made of platinum (Pt).

38. The film acoustic wave device according to claim 24, wherein the piezoelectric thin film is made of zinc oxide (ZnO).

39. The film acoustic wave device according to claim 24, wherein the piezoelectric thin film is made of aluminum nitride (AlN).

40. The film acoustic wave device according to claim 24, wherein an inductor is intended to be formed between the semiconductor substrate and the ground electrode.

41. A method of manufacturing a film acoustic wave device, comprising:

(a) forming a ground electrode intended to be placed on top of a semiconductor substrate which is made up of one of a plurality of pieces into which a wafer is divided;

(b) forming a piezoelectric thin film on top of the ground electrode; and

(c) forming at least one upper electrode on top of the piezoelectric thin film,

wherein a pattern of the film acoustic wave device is formed as a result of steps (a)-(c), and

wherein a shape of the pattern of the film acoustic wave device is dependent upon an intended position of the semiconductor substrate on the wafer.

42. The method of manufacturing a film acoustic wave device according to claim 41, wherein a length of the at least one upper electrode is dependent upon the intended position of the semiconductor substrate on the wafer.

a3 Cont

43. The method of manufacturing a film acoustic wave device according to claim 41, wherein a width of the at least one upper electrode is dependent upon the intended position of the semiconductor substrate on the wafer.

44. The method of manufacturing a film acoustic wave device according to claim 41, wherein the step of forming at least one upper electrode comprises forms a plurality of upper electrodes, and

wherein distances between each of the plurality of upper electrodes is dependent upon the intended position of the semiconductor substrate on the wafer.

45. The method of manufacturing a film acoustic wave device according to claim 41, wherein said step (c) further includes a step,

(c1) connecting the at least one upper electrode to a bonding pad, and

wherein a shape of the bonding pad is dependent upon the intended position of the semiconductor substrate on the wafer.

46. The method of manufacturing a film acoustic wave device according to claim 45, wherein an area covered by the bonding pad is dependent upon the intended position of the semiconductor substrate on the wafer.

a3 Cont

47. The film acoustic wave device according to claim 41, wherein said step (c) further includes steps,

(c1) connecting the at least one upper electrode to a bonding pad; and

(c2) connecting the at least one upper electrode and the bonding pad to a connecting pattern,

wherein a shape of the connecting pattern is dependent upon the intended position of the semiconductor substrate on the wafer.

48. The method of manufacturing a film acoustic wave device according to claim 47, wherein a length of the connecting pattern is dependent upon the intended position of the semiconductor substrate on the wafer.

49. The method of manufacturing a film acoustic wave device according to claim 47, wherein a width of the connecting pattern is dependent upon the intended position of the semiconductor substrate on the wafer.

50. The method of manufacturing a film acoustic wave device according to claim 41, wherein said step (c) further includes steps,

(c1) connecting the at least one upper electrode to a bonding pad; and

(c2) connecting the at least one upper electrode and the bonding pad to a connecting pattern,

wherein the connecting pattern is formed with an air bridge.

a3 Cont

51. The method of manufacturing a film acoustic wave device according to claim 41, further comprising a step,

(d) forming a capacitor on the same semiconductor substrate as the film acoustic wave device,

wherein a capacitance of the capacitor is dependent upon the intended position of the semiconductor substrate on the wafer.

52. The method of manufacturing a film acoustic wave device according to claim 41, wherein the semiconductor substrate is made of gallium arsenide (GaAs); the piezoelectric thin film is made of lead titanate ($PbTiO_3$); and the at least one upper electrode is a conductor substantially made of platinum (Pt).

53. The method of manufacturing a film acoustic wave device according to claim 41, wherein the semiconductor substrate is made of silicon (Si); the piezoelectric thin film is made of lead titanate ($PbTiO_3$); and the at least one upper electrode is a conductor substantially made of Platinum (Pt).

54. The method of manufacturing a film acoustic wave device according to claim 41, wherein the piezoelectric thin film is made of PZT ($PbTiO_3$-$PbZrO_3$); and the at least one upper electrode and the ground electrode is a conductor substantially made of platinum (Pt).

a3 Cont

55. The method of manufacturing a film acoustic wave device according to claim 41, wherein the piezoelectric thin film is made of zinc oxide (ZnO).

56. The method of manufacturing a film acoustic wave device according to claim 41, wherein the piezoelectric thin film is made of aluminum nitride (AlN).

57. The method of manufacturing a film acoustic wave device according to claim 41, wherein an inductor is intended to be formed between the semiconductor substrate and the ground electrode.

58. A method of manufacturing a circuit device comprising:

forming a plurality of elements intended to be placed on a substrate, such that the pattern shape formed by at least one of the plurality of elements is dependent upon a position on which the least one of the plurality of elements is intended to be formed on the substrate.

59. A circuit device manufactured according to the method of claim 58.--